

General Description

The TF070N06NG combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

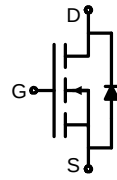
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

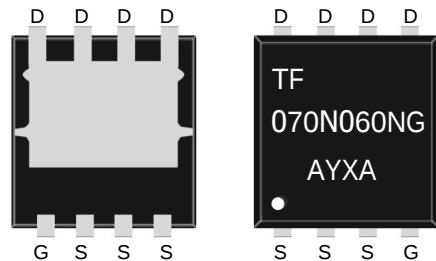
Product Summary



$$V_{DS} = 60V \quad I_D = 80A$$

$$R_{DS(ON)}(10V \text{ typ}) = 6.5m\Omega$$

$$R_{DS(ON)}(4.5V \text{ typ}) = 10m\Omega$$



PDFNWB5x6-8L

Ordering Information:

Part NO.	TF070N06NG
Marking 1	070N06NG:TF070N06NG
Marking 2	TF:tuofeng; Y:year code; X:Week; AA:device code;
MOQ	5000 PCS

Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	80	A
	$I_D @ T_C = 75^\circ C$	56	A
	$I_D @ T_C = 100^\circ C$	48	A
Pulsed Drain Current ①	I_{DM}	210	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	80	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	1.5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;



Single Pulse Avalanche Energy	E _{AS}	100			mJ	
Avalanche Current	I _{AS} I _{AR}	20			A	
●Thermal resistance						
Parameter	Symbol	Min.	Typ.	Max.	Unit	
Thermal resistance, junction - case	R _{thJC}	-	-	5.0	° C/W	
Thermal resistance, junction - ambient	R _{thJA}	-	-	63	° C/W	
Soldering temperature, wave soldering for 8s	T _{sold}	-	-	265	° C	
●Electronic Characteristics at T _J =25 (unless otherwise specified)						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V ,V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A		6.5	8.5	mΩ
		V _{GS} =4.5V, I _D =15A		10	12	mΩ
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =20A		15		S
Source-drain voltage	V _{SD}	I _S =20A			1.20	V
●Electronic Characteristics						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iss}	V _{ds} =30V,V _{gs} =0V f = 1MHz	-	895	-	pF
Output capacitance	C _{oss}		-	640	-	
Reverse transfer capacitance	C _{rss}		-	24.5	-	
●Gate Charge characteristics(T _a = 25°C)						
Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	R _g	f = 1MHz		1.4		Ω
Total gate charge	Q _g	V _{DD} = 30V I _D = 20A V _{GS} = 10V	-	23	-	nC
Gate - Source charge	Q _{gs}		-	3.2	-	
Gate - Drain charge	Q _{gd}		-	3.9	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} =30V ,V _{DS} =10V R _G =3.0Ω,I _D = 20A		7.3		ns
Turn-ON Rise time	t _r			30		ns
Turn-Off Delay time	t _{D(off)}			19		ns
Turn-Off Fall time	t _f			6.5		ns

Fig.1 Power Dissipation

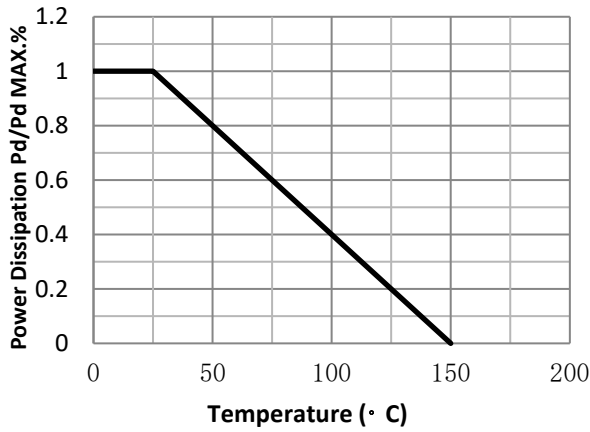


Fig.2 Typical output Characteristics

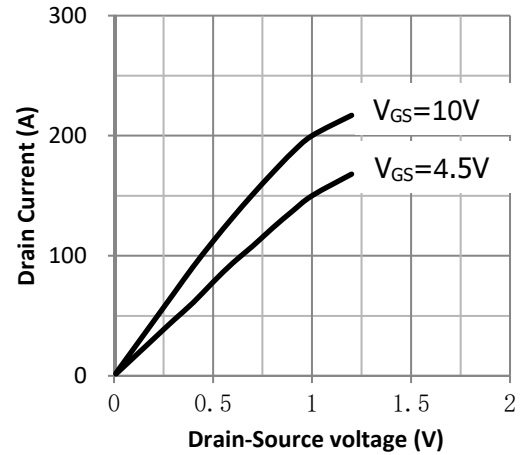


Fig.3 Threshold Voltage V.S Junction Temperature

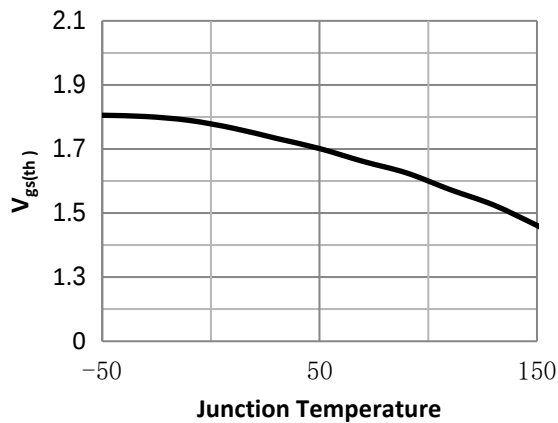


Fig.4 Resistance V.S Drain Current

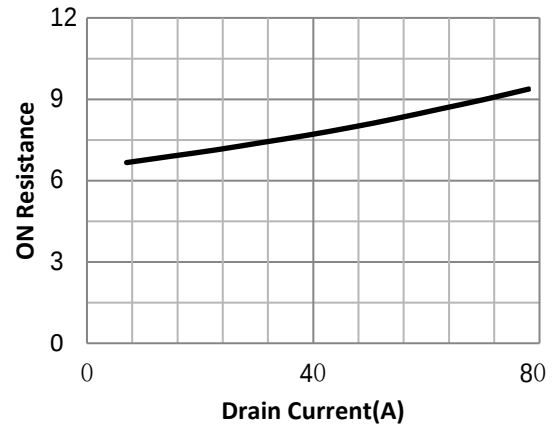


Fig.5 On-Resistance VS Drain Current

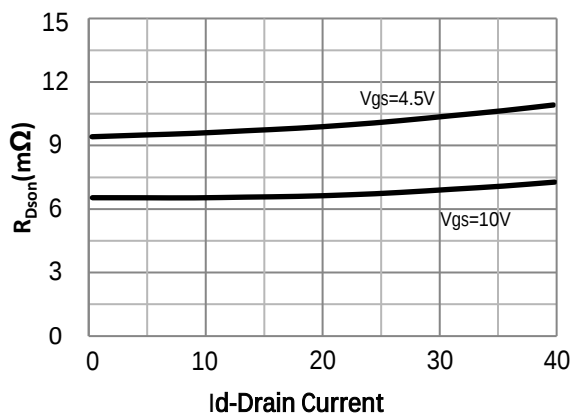


Fig.6 On-Resistance V.S Junction Temperature

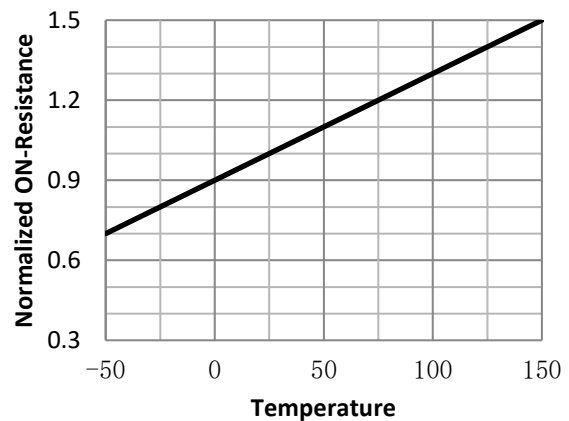


Fig.7 Switching Time Measurement Circuit

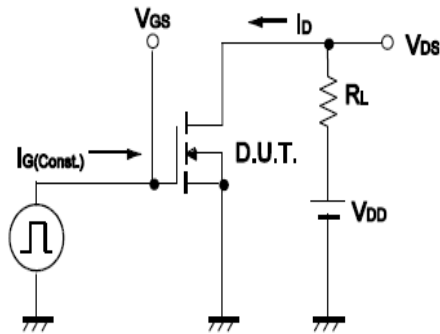


Fig.8 Gate Charge Waveform

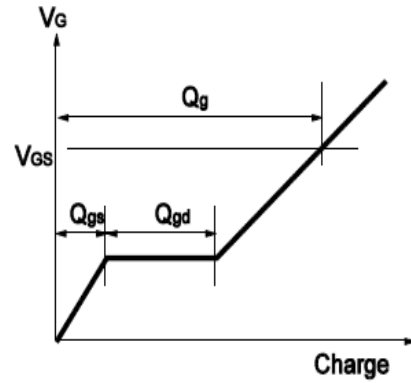


Fig.9 Switching Time Measurement Circuit

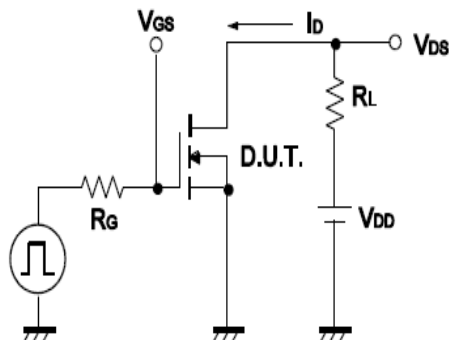


Fig.10 Gate Charge Waveform

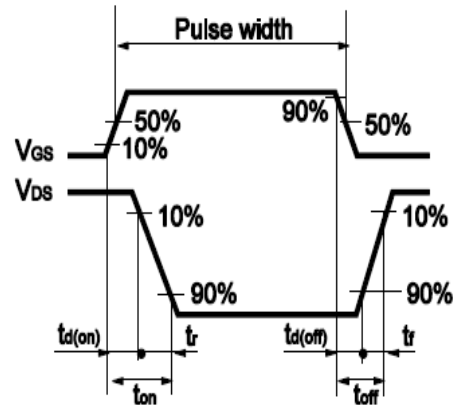


Fig.11 Avalanche Measurement Circuit

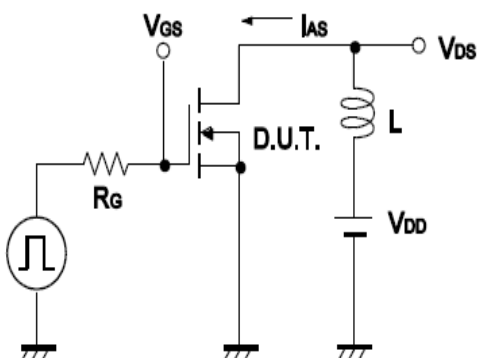
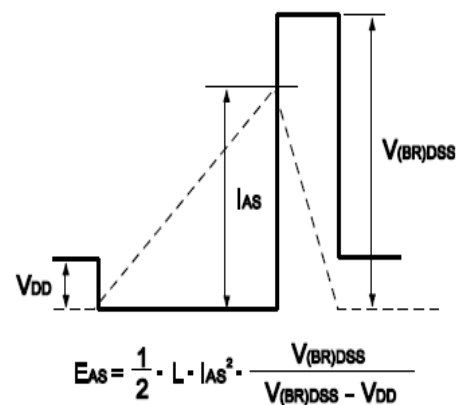
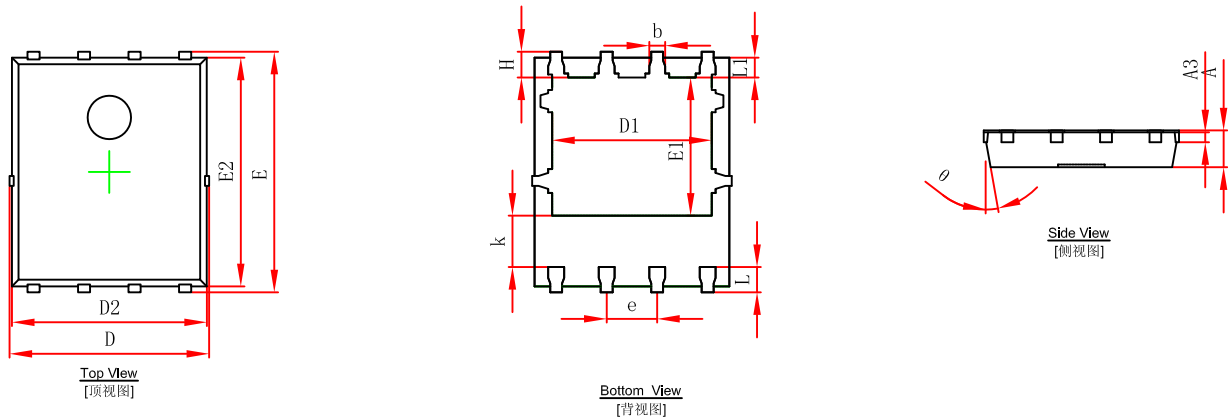


Fig.12 Avalanche Waveform

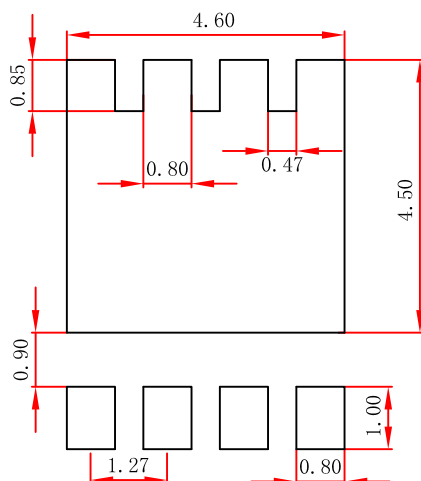


PDFNWB5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFNWB5x6-8L Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.